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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM® Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 600MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 653K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	1156-BBGA, FCBGA
Supplier Device Package	1156-FCBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu11eg-2ffvc1156e

Table 1: Absolute Maximum Ratings⁽¹⁾ (Cont'd)

Symbol	Description	Min	Max	Units
V_{CCO_PSDDR}	PS DDR I/O supply voltage.	-0.500	1.650	V
$V_{CC_PSDDR_PLL}$	PS DDR PLL supply voltage.	-0.500	2.000	V
V_{CCO_PSIO}	PS I/O supply.	-0.500	3.630	V
$V_{PSIN}^{(2)}$	PS I/O input voltage.	-0.500	$V_{CCO_PSIO} + 0.550$	V
	PS DDR I/O input voltage.	-0.500	$V_{CCO_PSDDR} + 0.550$	V
V_{CC_PSBATT}	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	-0.500	2.000	V
Programmable Logic (PL)				
V_{CCINT}	Internal supply voltage.	-0.500	1.000	V
$V_{CCINT_IO}^{(3)}$	Internal supply voltage for the I/O banks.	-0.500	1.000	V
V_{CCAUX}	Auxiliary supply voltage.	-0.500	2.000	V
V_{CCBRAM}	Supply voltage for the block RAM memories.	-0.500	1.000	V
V_{CCO}	Output drivers supply voltage for HD I/O banks.	-0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	-0.500	2.000	V
$V_{CCAUX_IO}^{(4)}$	Auxiliary supply voltage for the I/O banks.	-0.500	2.000	V
V_{REF}	Input reference voltage.	-0.500	2.000	V
$V_{IN}^{(2)(5)(7)}$	I/O input voltage for HD I/O banks. ⁽⁶⁾	-0.550	$V_{CCO} + 0.550$	V
	I/O input voltage for HP I/O banks.	-0.550	$V_{CCO} + 0.550$	V
I_{DC}	Available output current at the pad.	-20	20	mA
I_{RMS}	Available RMS output current at the pad.	-20	20	mA
GTH or GTY Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for transceiver circuits.	-0.500	1.000	V
$V_{MGTAVTT}$	Analog supply voltage for transceiver termination circuits.	-0.500	1.300	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	-0.500	1.900	V
$V_{MGTREFCLK}$	Transceiver reference clock absolute input voltage.	-0.500	1.300	V
$V_{MGTAVTRCAL}$	Analog supply voltage for the resistor calibration circuit of the transceiver column.	-0.500	1.300	V
V_{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	-0.500	1.200	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating. ⁽⁸⁾	-	10	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$.	-	10	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND. ⁽⁹⁾	-	0	mA
$I_{DCIN-PROG}$	DC input current for receiver input pins DC coupled RX termination = programmable. ⁽¹⁰⁾	-	0	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating.	-	6	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$.	-	6	mA

Table 4: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
$I_{CC_PSBATT}^{(4)(5)}$	Battery supply current at $V_{CC_PSBATT} = 1.50V$, RTC enabled.	–	–	3650	nA
	Battery supply current at $V_{CC_PSBATT} = 1.50V$, RTC disabled.	–	–	650	nA
	Battery supply current at $V_{CC_PSBATT} = 1.20V$, RTC enabled.	–	–	3150	nA
	Battery supply current at $V_{CC_PSBATT} = 1.20V$, RTC disabled.	–	–	150	nA
$I_{PSFS}^{(6)}$	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks ⁽⁸⁾ (measured per JEDEC specification)					
$R^{(9)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10% ⁽⁷⁾	120	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10% ⁽⁷⁾	240	+10% ⁽⁷⁾	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
$R^{(9)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
$R^{(9)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	$V_{CCO} \times 0.49$	$V_{CCO} \times 0.50$	$V_{CCO} \times 0.51$	V
	70% V_{CCO}	$V_{CCO} \times 0.69$	$V_{CCO} \times 0.70$	$V_{CCO} \times 0.71$	V

Table 4: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	-35%	100	+35%	Ω
n	Temperature diode ideality factor.	-	1.026	-	-
r	Temperature diode series resistance.	-	2	-	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 μA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)).

Table 5: PS MIO Pull-up and Pull-down Current

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO_PSMIO} = 3.3V$.	20	80	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO_PSMIO} = 2.5V$.	20	80	μA
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CCO_PSMIO} = 1.8V$.	15	65	μA
I_{RPD}	Pad pull-down (when selected) at $V_{IN} = 3.3V$.	20	80	μA
	Pad pull-down (when selected) at $V_{IN} = 2.5V$.	20	80	μA
	Pad pull-down (when selected) at $V_{IN} = 1.8V$.	15	65	μA

PL I/O Levels

Table 14: SelectIO DC Input and Output Levels For HD I/O Banks⁽¹⁾⁽²⁾⁽³⁾

I/O Standard	V _{IL}		V _{IH}		V _{OL}	V _{OH}	I _{OL}	I _{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	-0.300	V _{REF} - 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	0.400	V _{CCO} - 0.400	8.0	-8.0
HSTL_I_18	-0.300	V _{REF} - 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	0.400	V _{CCO} - 0.400	8.0	-8.0
HSUL_12	-0.300	V _{REF} - 0.130	V _{REF} + 0.130	V _{CCO} + 0.300	20% V _{CCO}	80% V _{CCO}	0.1	-0.1
LVCMOS12	-0.300	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.300	0.400	V _{CCO} - 0.400	Note 4	Note 4
LVCMOS15	-0.300	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.300	0.450	V _{CCO} - 0.450	Note 5	Note 5
LVCMOS18	-0.300	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.300	0.450	V _{CCO} - 0.450	Note 5	Note 5
LVCMOS25	-0.300	0.700	1.700	V _{CCO} + 0.300	0.400	V _{CCO} - 0.400	Note 5	Note 5
LVCMOS33	-0.300	0.800	2.000	3.400	0.400	V _{CCO} - 0.400	Note 5	Note 5
LVTTL	-0.300	0.800	2.000	3.400	0.400	2.400	Note 5	Note 5
SSTL12	-0.300	V _{REF} - 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	V _{CCO} /2 - 0.150	V _{CCO} /2 + 0.150	14.25	-14.25
SSTL135	-0.300	V _{REF} - 0.090	V _{REF} + 0.090	V _{CCO} + 0.300	V _{CCO} /2 - 0.150	V _{CCO} /2 + 0.150	8.9	-8.9
SSTL135_II	-0.300	V _{REF} - 0.090	V _{REF} + 0.090	V _{CCO} + 0.300	V _{CCO} /2 - 0.150	V _{CCO} /2 + 0.150	13.0	-13.0
SSTL15	-0.300	V _{REF} - 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	V _{CCO} /2 - 0.175	V _{CCO} /2 + 0.175	8.9	-8.9
SSTL15_II	-0.300	V _{REF} - 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	V _{CCO} /2 - 0.175	V _{CCO} /2 + 0.175	13.0	-13.0
SSTL18_I	-0.300	V _{REF} - 0.125	V _{REF} + 0.125	V _{CCO} + 0.300	V _{CCO} /2 - 0.470	V _{CCO} /2 + 0.470	8.0	-8.0
SSTL18_II	-0.300	V _{REF} - 0.125	V _{REF} + 0.125	V _{CCO} + 0.300	V _{CCO} /2 - 0.600	V _{CCO} /2 + 0.600	13.4	-13.4
MIPI_DPHY_DCI_LP ⁽⁶⁾	-0.300	0.550	0.880	V _{CCO} + 0.300	0.050	1.100	0.01	-0.01

Notes:

- Tested according to relevant specifications.
- Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)).
- POD10 and POD12 DC input and output levels are shown in [Table 16](#), [Table 20](#), [Table 21](#), and [Table 22](#).
- Supported drive strengths of 4, 8, or 12 mA in HD I/O banks.
- Supported drive strengths of 4, 8, 12, or 16 mA in HD I/O banks.
- Low-power option for MIPI_DPHY_DCI.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in the Vivado® Design Suite as outlined in [Table 25](#).

Table 25: Speed Specification Version By Device

2017.1	Device
1.08	XCZU4CG, XCZU4EG, XCZU4EV, XCZU5CG, XCZU5EG, XCZU5EV, XCZU11EG
1.10	XCZU2CG, XCZU2EG, XCZU3CG, XCZU3EG, XCZU6CG, XCZU6EG, XCZU7CG, XCZU7EG, XCZU7EV, XCZU9CG, XCZU9EG, XCZU15EG, XCZU17EG, XCZU19EG

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Zynq UltraScale+ MPSoC.

Table 31: PS NAND NV-DDR Synchronous Performance

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
NV-DDR ⁽¹⁾	5	200	200	200	Mb/s
	4	166.6	166.6	166.6	Mb/s
	3	133.3	133.3	133.3	Mb/s
	2	100	100	100	Mb/s
	1	66.6	66.6	66.6	Mb/s
	0	40	40	40	Mb/s

Notes:

1. The PS NAND memory controller interface for NV-DDR switching characteristics meets the requirements of the ONFI 3.1 specification.

Table 32: PS NAND SDR Asynchronous Performance

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
SDR ⁽¹⁾⁽²⁾	5	50	50	50	Mb/s
	4	40	40	40	Mb/s
	3	33.3	33.3	33.3	Mb/s
	2	28.5	28.5	28.5	Mb/s
	1	20	20	20	Mb/s
	0	10	10	10	Mb/s

Notes:

1. The PS NAND memory controller interface for SDR switching characteristics meets the requirements of the ONFI 3.1 specification.
2. The NAND controller reference clock frequency maximum is 83 MHz.

Table 33: PS-PL Interface Performance

Symbol	Description	Min	Max	Units
FEMIOGEMCLK	EMIO gigabit Ethernet controller maximum frequency.	–	125	MHz
FEMIOSDCLK	EMIO SD controller maximum frequency.	–	25	MHz
FEMIOSPICLK	EMIO SPI controller maximum frequency.	–	25	MHz
FEMIOTRACECLK	EMIO trace controller maximum frequency.	–	125	MHz
FFCIDDMACLK	Flow control interface DMA maximum frequency.	–	333	MHz
FAXICLK	Maximum AXI interface performance.	–	333	MHz
FDPLIVEVIDEO	DisplayPort controller live video interface maximum frequency.	–	300	MHz

PS Switching Characteristics

PS Clocks

Table 34: PS Reference Clock Requirements⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
T _{RMSJPSCLK}	PS_REF_CLK input RMS clock jitter.	–	–	3	ps
T _{PJPSCLK}	PS_REF_CLK input period jitter (peak-to-peak). Number of clock cycles = 10,000	–	–	50	ps
T _{DCPSCLK}	PS_REF_CLK duty cycle.	45	–	55	%
T _{RFPSCLK}	PS_REF_CLK rise time (20%–80%) and fall time (80%–20%).	–	–	2.22	ns
F _{PSCLK}	PS_REF_CLK frequency.	27	–	60	MHz

Notes:

1. The values in this table are applicable to alternative PS reference clock inputs ALT_REF_CLK, AUX_REF_CLK, and VIDEO_CLK.

Table 35: PS RTC Crystal Requirements⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
F _{XTAL}	Parallel resonance crystal frequency.	–	32.8	–	KHz
T _{FTXTAL}	Frequency tolerance.	–20	–	20	ppm
C _{XTAL}	Load capacitance for crystal parallel resonance.	–	12.5	–	pF
R _{ESR}	Crystal ESR (16.8 and 19.2 MHz).	–	70	–	KΩ
C _{SHUNT}	Crystal shunt capacitance.	–	1.4	–	pF

Notes:

1. Required board components: Feedback resistor = 4.7 MΩ, PCB and pad capacitance = 1.5 pF, C₁ and C₂ capacitance = 21 pF.

Table 36: PS PLL Switching Characteristics

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F _{LOCKPSPLL}	PLL maximum lock time.	100	100	100	μs
F _{PSPLLMAX}	PLL maximum output frequency.	1600	1600	1600	MHz
F _{PSPLLMIN}	PLL minimum output frequency.	750	750	750	MHz
F _{PSPLLVCOMAX}	PLL maximum VCO frequency.	3000	3000	3000	MHz
F _{PSPLLVCOMIN}	PLL minimum VCO frequency.	1500	1500	1500	MHz

PS Gigabit Ethernet Controller Interface

Table 44: RGMII Interface⁽¹⁾

Symbol	Description	Min	Max	Units
T _{DGEMTXCLK}	Transmit clock duty cycle.	45	55	%
T _{GEMTXCKO}	TXD output clock to out time.	-0.5	0.5	ns
T _{GEMRXDCK}	RXD input setup time.	0.8	—	ns
T _{GEMRXCKD}	RXD input hold time.	0.8	—	ns
T _{MdioCLK}	MDC output clock period.	400	—	ns
T _{MdioCKL}	MDC low time.	160	—	ns
T _{MdioCKH}	MDC high time.	160	—	ns
T _{MdiODCK}	MDIO input data setup time.	80	—	ns
T _{MdiOCKD}	MDIO input data hold time.	0.0	—	ns
T _{MdiOCKO}	MDIO output data delay time.	-1.0	15	ns
F _{GETXCLK}	RGMII_TX_CLK transmit clock frequency.	—	125	MHz
F _{GERXCLK}	RGMII_RX_CLK receive clock frequency.	—	125	MHz
F _{ENET_REF_CLK}	Ethernet reference clock frequency.	—	125	MHz

Notes:

1. The test conditions are configured to the LVCMS 2.5V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS SD/SDIO Controller Interface

Table 45: SD/SDIO Interface⁽¹⁾

Symbol	Description	Min	Max	Units
SD/SDIO Interface DDR50 Mode				
T _{DCDDRCLK}	SD device clock duty cycle.	45	55	%
T _{SDDDRCK01}	Clock to output delay, data. ⁽²⁾	1.0	6.8	ns
T _{SDDRIVW}	Input valid data window. ⁽³⁾	3.5	—	ns
T _{SDDDRDCK2}	Input setup time, command.	4.7	—	ns
T _{SDDDRCKD2}	Input hold time, command.	1.5	—	ns
T _{SDDDRCK02}	Clock to output delay, command.	1.0	13.8	ns
F _{SDDDRCLK}	High-speed mode SD device clock frequency.	—	50	MHz
SD/SDIO Interface SDR104				
T _{DCSDHSCLK1}	SD device clock duty cycle.	40	60	%
T _{SDSDRCK01}	Clock to output delay, all outputs. ⁽²⁾	1.0	3.2	ns
T _{SDSDR1IVW}	Input valid data window. ⁽³⁾	0.5	—	UI
F _{SDSDRCLK1}	SDR104 mode device clock frequency.	—	200	MHz
SD/SDIO Interface SDR50/25				
T _{DCSDHSCLK2}	SD device clock duty cycle.	40	60	%
T _{SDSDRCK02}	Clock to output delay, all outputs. ⁽²⁾	1.0	6.8	ns
T _{SDSDR2IVW}	Input valid data window. ⁽³⁾	0.3	—	UI

PS I2C Controller Interface

Table 47: I2C Interface⁽¹⁾

Symbol	Description	Min	Max	Units
I2C Fast-mode Interface				
T _{I2CFCKL}	SCL Low time.	1.3	–	μs
T _{I2CFCKH}	SCL High time.	0.6	–	μs
T _{I2CFCKO}	SDA clock to out delay.	–	900	ns
T _{I2CFDCK}	SDA input setup time.	100	–	ns
F _{I2CFCLK}	SCL clock frequency.	–	400	KHz
I2C Standard-mode Interface				
T _{I2CSCKL}	SCL Low time.	4.7	–	μs
T _{I2CSCKH}	SCL High time.	4.0	–	μs
T _{I2CSCKO}	SDA clock to out delay.	–	3450	ns
T _{I2CSDCK}	SDA input setup time.	250	–	ns
F _{I2CSCLK}	SCL clock frequency.	–	100	KHz

Notes:

1. The test conditions are configured to the LVC MOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS Triple-timer Counter Interface

Table 54: Triple-timer Counter Interface

Symbol	Description	Min	Max	Units
$T_{PWTTCOCLK}$	Triple-timer counter output clock pulse width.	60.4	–	ns
$F_{TTCOCLK}$	Triple-timer counter output clock frequency.	–	16.5	MHz
$T_{TTCICLKL}$	Triple-timer counter input clock high pulse width.	$1.5 \times F_{LPD_LSBUS_CTRLMAX}$	–	ns
$T_{TTCICLKH}$	Triple-timer counter input clock low pulse width.	$1.5 \times F_{LPD_LSBUS_CTRLMAX}$	–	ns
$F_{TTCICLK}$	Triple-timer counter input clock frequency.	–	$F_{LPD_LSBUS_CTRLMAX}/3$	MHz

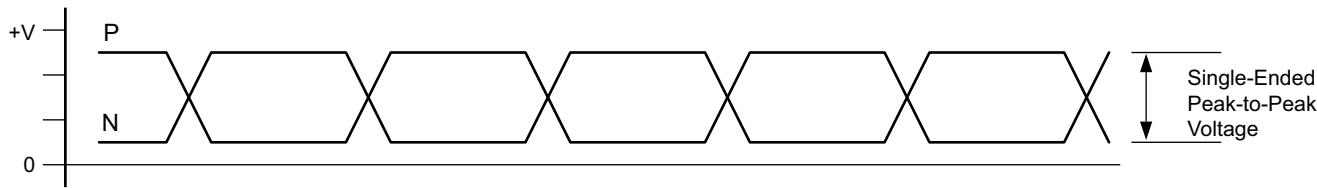
Notes:

1. All timing values assume an ideal external input clock. Your actual timing budget must account for additional external clock jitter.

PS Watchdog Timer Interface

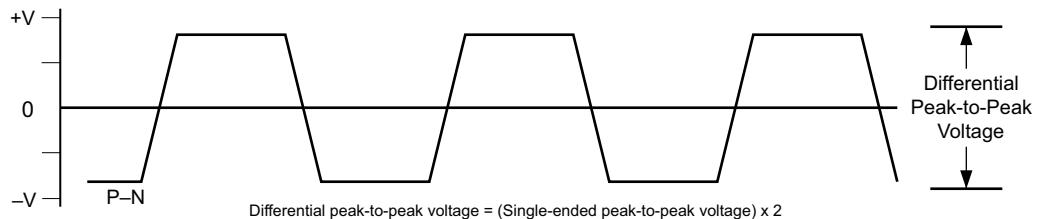
Table 55: Watchdog Timer Interface

Symbol	Description	Min	Max	Units
F_{WDTCLK}	Watchdog timer input clock frequency.	–	100	MHz



X16653-101316

Figure 3: Single-Ended Peak-to-Peak Voltage



X16639-101316

Figure 4: Differential Peak-to-Peak Voltage

[Table 95](#) and [Table 96](#) summarize the DC specifications of the GTH transceivers input and output clocks in Zynq UltraScale+ MPSoC. Consult the *UltraScale Architecture GTH Transceiver User Guide* ([UG576](#)) for further details.

Table 95: GTH Transceiver Clock Input Level Specification

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage.	250	—	2000	mV
R_{IN}	Differential input resistance.	—	100	—	Ω
C_{EXT}	Required external AC coupling capacitor.	—	10	—	nF

Table 96: GTH Transceiver Clock Output Level Specification

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N.	$R_T = 100\Omega$ across P and N signals	100	—	330	mV
V_{OH}	Output High voltage for P and N.	$R_T = 100\Omega$ across P and N signals	500	—	700	mV
V_{DDOUT}	Differential output voltage. (P-N), P = High (N-P), N = High	$R_T = 100\Omega$ across P and N signals	300	—	430	mV
V_{CMOUT}	Common mode voltage.	$R_T = 100\Omega$ across P and N signals	300	—	500	mV

Table 105: GTH Transceiver Protocol List

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
CAUI-10	IEEE 802.3-2012	10.3125	Compliant
nPPI	IEEE 802.3-2012	10.3125	Compliant
10GBASE-KR ⁽¹⁾	IEEE 802.3-2012	10.3125	Compliant
40GBASE-KR	IEEE 802.3-2012	10.3125	Compliant
SFP+	SFF-8431 (SR and LR)	9.95328–11.10	Compliant
XFP	INF-8077i, revision 4.5	10.3125	Compliant
RXAUI	CEI-6G-SR	6.25	Compliant
XAUI	IEEE 802.3-2012	3.125	Compliant
1000BASE-X	IEEE 802.3-2012	1.25	Compliant
5.0G Ethernet	IEEE 802.3bx (PAR)	5	Compliant
2.5G Ethernet	IEEE 802.3bx (PAR)	2.5	Compliant
HiGig, HiGig+, HiGig2	IEEE 802.3-2012	3.74, 6.6	Compliant
OTU2	ITU G.8251	10.709225	Compliant
OTU4 (OTL4.10)	OIF-CEI-11G-SR	11.180997	Compliant
OC-3/12/48/192	GR-253-CORE	0.1555–9.956	Compliant
TFI-5	OIF-TFI5-0.1.0	2.488	Compliant
Interlaken	OIF-CEI-6G, OIF-CEI-11G-SR	4.25–12.5	Compliant
PCIe Gen1, 2, 3	PCI Express base 3.0	2.5, 5.0, and 8.0	Compliant
SDI ⁽²⁾	SMPTE 424M-2006	0.27–2.97	Compliant
UHD-SDI ⁽²⁾	SMPTE ST-2081 6G, SMPTE ST-2082 12G	6 and 12	Compliant
Hybrid memory cube (HMC)	HMC-15G-SR	10, 12.5, and 15.0	Compliant
MoSys Bandwidth Engine	CEI-11-SR and CEI-11-SR (overclocked)	10.3125, 15.5	Compliant
CPRI	CPRI_v_6_1_2014-07-01	0.6144–12.165	Compliant
HDMI ⁽²⁾	HDMI 2.0	All	Compliant
Passive optical network (PON)	10G-EAPON, 1G-EAPON, NG-PON2, XG-PON, and 2.5G-PON	0.155–10.3125	Compliant
JESD204a/b	OIF-CEI-6G, OIF-CEI-11G	3.125–12.5	Compliant
Serial RapidIO	RapidIO specification 3.1	1.25–10.3125	Compliant
DisplayPort ⁽²⁾	DP 1.2B CTS	1.62–5.4	Compliant
Fibre channel	FC-PI-4	1.0625–14.025	Compliant
SATA Gen1, 2, 3	Serial ATA revision 3.0 specification	1.5, 3.0, and 6.0	Compliant
SAS Gen1, 2, 3	T10/BSR INCITS 519	3.0, 6.0, and 12.0	Compliant
SFI-5	OIF-SFI5-01.0	0.625–12.5	Compliant
Aurora	CEI-6G, CEI-11G-LR	up to 11.180997	Compliant

Notes:

1. The transition time of the transmitter is faster than the IEEE Std 802.3-2012 specification.
2. This protocol requires external circuitry to achieve compliance.

Table 113: GTY Transceiver PLL/Lock Time Adaptation

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T _{LOCK}	Initial PLL lock.		—	—	1	ms
T _{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	—	50,000	37 x 10 ⁶	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		—	50,000	2.3 x 10 ⁶	UI

Table 114: GTY Transceiver User Clock Switching Characteristics⁽¹⁾

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V _{CCINT} Operating Voltages					Units	
				0.90V	0.85V		0.72V			
		Internal Logic	Interconnect Logic	-3 ⁽²⁾	-2 ⁽²⁾⁽³⁾	-1 ⁽⁴⁾⁽⁵⁾	-2 ⁽³⁾	-1 ⁽⁵⁾		
F _{TXOUTPMA}	TXOUTCLK maximum frequency sourced from OUTCLKPMA	511.719	511.719	402.833	402.833	322.266	322.266	MHz		
F _{RXOUTPMA}	RXOUTCLK maximum frequency sourced from OUTCLKPMA	511.719	511.719	402.833	402.833	322.266	322.266	MHz		
F _{TXOUTPROGDIV}	TXOUTCLK maximum frequency sourced from TXPROGDIVCLK	511.719	511.719	511.719	511.719	511.719	511.719	MHz		
F _{RXOUTPROGDIV}	RXOUTCLK maximum frequency sourced from RXPROGDIVCLK	511.719	511.719	511.719	511.719	511.719	511.719	MHz		
F _{TXIN}	TXUSRCLK ⁽⁶⁾ maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz	
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz	
		64	64, 128	511.719	440.781	402.832	402.832	195.313	MHz	
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz	
		40	40, 80	409.375	409.375	312.500	350.000	257.813	MHz	
		80	80, 160	409.375	352.625	322.266	352.625	156.250	MHz	
F _{RXIN}	RXUSRCLK ⁽⁶⁾ maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz	
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz	
		64	64, 128	511.719	440.781	402.832	402.832	195.313	MHz	
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz	
		40	40, 80	409.375	409.375	312.500	350.000	257.813	MHz	
		80	80, 160	409.375	352.625	322.266	352.625	156.250	MHz	

Table 115: GTY Transceiver Transmitter Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units
F _{GTYTX}	Serial data rate range		0.500	–	F _{GTYMAX}	Gb/s
T _{RTX}	TX rise time	20%–80%	–	21	–	ps
T _{FTX}	TX fall time	80%–20%	–	21	–	ps
T _{LSSKEW}	TX lane-to-lane skew ⁽¹⁾		–	–	500.00	ps
T _{J32.75}	Total jitter ⁽²⁾⁽⁴⁾	32.75 Gb/s	–	–	0.35	UI
D _{J32.75}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.19	UI
T _{J28.21}	Total jitter ⁽²⁾⁽⁴⁾	28.21 Gb/s	–	–	0.28	UI
D _{J28.21}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J16.375}	Total jitter ⁽²⁾⁽⁴⁾	16.375 Gb/s	–	–	0.28	UI
D _{J16.375}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J15.0}	Total jitter ⁽²⁾⁽⁴⁾	15.0 Gb/s	–	–	0.28	UI
D _{J15.0}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.1 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.025 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J13.1}	Total jitter ⁽²⁾⁽⁴⁾	13.1 Gb/s	–	–	0.28	UI
D _{J13.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	12.5 Gb/s	–	–	0.28	UI
D _{J12.5_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	12.5 Gb/s	–	–	0.33	UI
D _{J12.5_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J11.3_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	11.3 Gb/s	–	–	0.28	UI
D _{J11.3_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.28	UI
D _{J10.3125_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.33	UI
D _{J10.3125_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	9.953 Gb/s	–	–	0.28	UI
D _{J9.953_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	9.953 Gb/s	–	–	0.33	UI
D _{J9.953_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J8.0}	Total jitter ⁽³⁾⁽⁴⁾	8.0 Gb/s	–	–	0.32	UI
D _{J8.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J6.6}	Total jitter ⁽³⁾⁽⁴⁾	6.6 Gb/s	–	–	0.30	UI
D _{J6.6}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J5.0}	Total jitter ⁽³⁾⁽⁴⁾	5.0 Gb/s	–	–	0.30	UI
D _{J5.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J4.25}	Total jitter ⁽³⁾⁽⁴⁾	4.25 Gb/s	–	–	0.30	UI
D _{J4.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI

Table 119: Maximum Performance for Interlaken 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s Protocol and Lane Logic Mode Designs

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages								Units	
		0.90V		0.85V			0.72V				
		-3 ⁽¹⁾	-2 ⁽¹⁾	-1	-2	-1					
F _{RX_SERDES_CLK}	Receive serializer/deserializer clock	440.79	440.79	N/A	402.84	N/A				MHz	
F _{TX_SERDES_CLK}	Transmit serializer/deserializer clock	440.79	440.79	N/A	402.84	N/A				MHz	
F _{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	N/A	250.00	N/A				MHz	
		Min ⁽²⁾	Max	Min ⁽²⁾	Max	Min	Max	Min ⁽²⁾	Max	Min Max	
F _{CORE_CLK}	Interlaken core clock	412.50 ⁽³⁾	479.20	412.50 ⁽³⁾	479.20	N/A	412.50	429.69	N/A	MHz	
F _{LBUS_CLK}	Interlaken local bus clock	300.00 ⁽⁴⁾	349.52	300.00 ⁽⁴⁾	349.52	N/A	300.00	349.52	N/A	MHz	

Notes:

1. 6 x 28.21 mode is only supported in the -2 (V_{CCINT}=0.85V) and -3 (V_{CCINT}=0.90V) speed grades.
2. These are the minimum clock frequencies at the maximum lane performance.
3. The minimum value for CORE_CLK is 451.36 MHz for the 6 x 28.21 Gb/s protocol.
4. The minimum value for LBUS_CLK is 330.00 MHz for the 6 x 28.21 Gb/s protocol.

Table 120: Maximum Performance for Interlaken 12 x 25.78125 Gb/s Lane Logic Only Mode Designs

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages								Units	
		0.90V		0.85V			0.72V				
		-3	-2	-1	-2	-1					
F _{RX_SERDES_CLK}	Receive serializer/deserializer clock	402.84	402.84	N/A	N/A	N/A				MHz	
F _{TX_SERDES_CLK}	Transmit serializer/deserializer clock	402.84	402.84	N/A	N/A	N/A				MHz	
F _{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	N/A	N/A	N/A				MHz	
F _{CORE_CLK}	Interlaken core clock	412.50	412.50	N/A	N/A	N/A				MHz	
F _{LBUS_CLK}	Interlaken local bus clock	349.52	349.52	N/A	N/A	N/A				MHz	

Video Codec Performance

The *UltraScale Architecture and Product Overview* ([DS890](#)) lists the Zynq UltraScale+ MPSoC EV devices that include the Video Codec unit (VCU).

Table 123: VCU Performance

Description	Speed Grade and V_{CCINT} Operating Voltages					Units	
	0.90V	0.85V		0.72V			
	-3	-2	-1	-2	-1		
Video Codec decoder block maximum frequency (H.264/5 10-bit 4:2:2)	667	667	667	667	667	MHz	

PL System Monitor Specifications

Table 124: PL SYSMON Specifications

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
$V_{CCADC} = 1.8V \pm 3\%$, $V_{REFP} = 1.25V$, $V_{REFN} = 0V$, $ADCCLK = 5.2$ MHz, $T_j = -40^{\circ}C$ to $100^{\circ}C$, typical values at $T_j = 40^{\circ}C$						
ADC Accuracy⁽¹⁾						
Resolution			10	–	–	Bits
Integral nonlinearity ⁽²⁾	INL		–	–	± 1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	± 1	LSBs
Offset error		Offset calibration enabled	–	–	± 2	LSBs
Gain error			–	–	± 0.4	%
Sample rate			–	–	0.2	MS/s
RMS code noise		External 1.25V reference	–	–	1	LSBs
		On-chip reference	–	1	–	LSBs
ADC Accuracy at Extended Temperatures						
Resolution		$T_j = -55^{\circ}C$ to $125^{\circ}C$	10	–	–	Bits
Integral nonlinearity ⁽²⁾	INL	$T_j = -55^{\circ}C$ to $125^{\circ}C$	–	–	± 1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic ($T_j = -55^{\circ}C$ to $125^{\circ}C$)	–	–	± 1	
Analog Inputs⁽²⁾						
ADC input ranges		Unipolar operation	0	–	1	V
		Bipolar operation	-0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent channels set within these ranges should not corrupt measurements on adjacent channels	-0.1	–	V_{CCADC}	V

Configuration Switching Characteristics

Table 127: Configuration Switching Characteristics

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units	
		0.90V		0.85V		0.72V		
		-3	-2	-1	-2	-1		
PL Power-up Timing Characteristics								
T _{PL}	PS_PROG_B PL latency.	7.5	7.5	7.5	7.5	7.5	ms, Max	
T _{POR}	Power-on reset from PL power-on to PL ready to configure (40 ms maximum ramp rate).	65	65	65	65	65	ms, Max	
		0	0	0	0	0	ms, Min	
T _{PS_PROG_B}	Power-on reset from PL power-on to PL ready to configure with POR override (2 ms maximum ramp rate).	15	15	15	15	15	ms, Max	
		5	5	5	5	5	ms, Min	
T _{PS_PROG_B}	PL program pulse width.	250	250	250	250	250	ns, Min	
Internal Configuration Access Port								
F _{ICAPCK}	Internal configuration access port (ICAPE3).	200	200	200	150	150	MHz, Max	
DNA Port Switching								
F _{DNACK}	DNA port frequency (DNA_PORT).	200	200	200	175	175	MHz, Max	
STARTUPE3 Ports								
F _{CFGMCLK}	STARTUPE3 CFGMCLK output frequency.	50.00	50.00	50.00	50.00	50.00	MHz, Typ	
F _{CFGMCLKTOL}	STARTUPE3 CFGMCLK output frequency tolerance.	±15	±15	±15	±15	±15	%, Max	
T _{DCI_MATCH}	Specifies a stall in the startup cycle until the digitally controlled impedance (DCI) match signals are asserted.	4	4	4	4	4	ms, Max	